CSD87335Q3D 同步降压 NexFET™ 电源块

1 特性

- 半桥电源块
- V_{IN} 高达 27V
- 15A 电流时系统效率达 93.5%
- 工作电流高达 25A
- 高频工作（高达 1.5MHz）
- 高密度 3.3mm × 3.3mm 小外形尺寸无引线 (SON) 封装
- 针对 5V 栅极驱动进行了优化
- 低开关损耗
- 超低电感封装
- 符合 RoHS 标准
- 无卤素
- 无铅引脚镀层

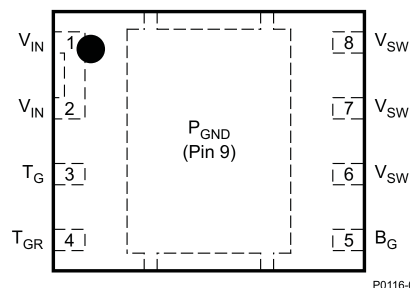
2 应用范围

- 同步降压转换器
  - 高频 应用
  - 高电流、低占空比 应用
- 多相位同步降压转换器
- 负载点 (POL) 直流 - 直流转换器
- IMVP、VRM 和 VRD 应用

3 说明

CSD87335Q3D NexFET™电源块是面向同步降压 应用 的优化设计方案，能够以 3.3mm × 3.3mm 的小巧外形提供高电流、高效率以及高频率性能。该产品针对 5V 栅极驱动 应用进行了优化，可提供一套灵活的解决方案，在与来自外部控制器/驱动器的任一 5V 栅极驱动配套使用时，均可提供高密度电源。

顶视图

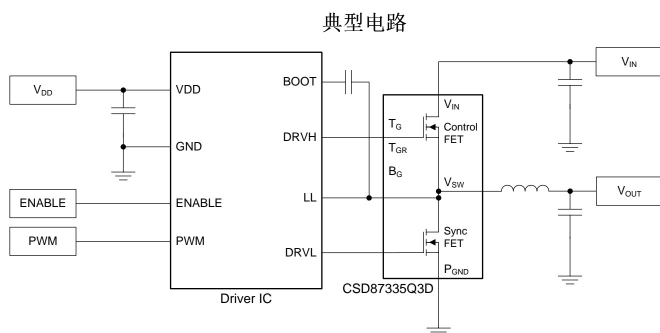


订购信息(1)

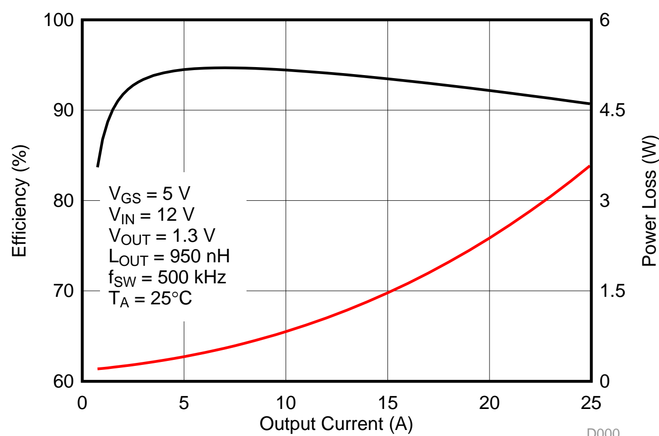
器件	介质	数量	封装	出货
CSD87335Q3D	13 英寸卷带	2500	SON 3.3mm × 3.3mm 塑料封装	卷带式
CSD87335Q3DT	7 英寸卷带	250		

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

典型电路



典型电源块效率与功率损耗



An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

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4 修订历史记录

日期	修订版本	注释
2016 年2 月	*	最初发布。

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5 Specifications

5.1 Absolute Maximum Ratings

T_A = 25°C (unless otherwise noted)[1]

		MIN	MAX	UNIT
Voltage	V_{IN} to P_{GND}		30	V
	V_{SW} to P_{GND}		30	V
	V_{SW} to P_{GND} (10 ns)		32	V
	T_G to T_{GR}	–8	10	V
	B_G to P_{GND}	–8	10	V
Pulsed current rating, I_{DM}[2]			70	A
Power dissipation, P_D			6	W
Avalanche energy E_{AS}	Sync FET, I_D = 51 A, L = 0.1 mH		130	mJ
	Control FET, I_D = 33 A, L = 0.1 mH		54	mJ
Operating junction and storage temperature, T_J, T_{STG}		–55	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) Pulse duration ≤ 50 μs, duty cycle ≤ 1%.

5.2 Recommended Operating Conditions

T_A = 25° (unless otherwise noted)

		MIN	MAX	UNIT
Gate drive voltage, V_{GS}		4.5	8	V
Input supply voltage, V_{IN}			27	V
Switching frequency, f_{SW}	C_{BST} = 0.1 μF (min)		1500	kHz
Operating current			25	A
Operating temperature, T_J			125	°C

5.3 Thermal Information

T_A = 25°C (unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{θJA}$	Junction-to-ambient thermal resistance (Min Cu)[1]			135	°C/W
	Junction-to-ambient thermal resistance (Max Cu)[1][2]			73	°C/W
$R_{θJC}$	Junction-to-case thermal resistance (Top of package)[1]			29	°C/W
	Junction-to-case thermal resistance (P_{GND} Pin)[1]			2.5	°C/W

(1) $R_{θJC}$ is determined with the device mounted on a 1 inch^2 (6.45 cm^2), 2 oz. (0.071 mm thick) Cu pad on a 1.5 inch × 1.5 inch (3.81 cm × 3.81 cm), 0.06 inch (1.52 mm) thick FR4 board. $R_{θJC}$ is specified by design while $R_{θJA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1 inch^2 (6.45 cm^2) Cu.

5.4 Power Block Performance[1]

T_A = 25° (unless otherwise noted)

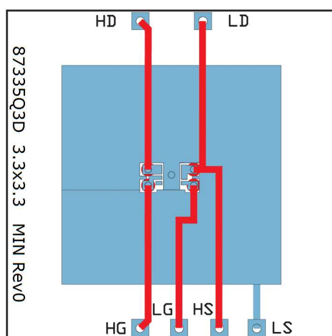
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Power loss, P_{LOSS}[1]	V_{IN} = 12 V, V_{GS} = 5 V, V_{OUT} = 1.3 V, I_{OUT} = 15 A, f_{SW} = 500 kHz, L_{OUT} = 950 nH, T_J = 25ºC		1.5		W
V_{IN} Quiescent current, I_{QVIN}	T_G to T_{GR} = 0 V, B_G to P_{GND} = 0 V		10		μA

(1) Measurement made with six 10 μF (TDK C3216X5R1C106KT or equivalent) ceramic capacitors placed across V_{IN} to P_{GND} pins and using a high current 5 V driver IC.

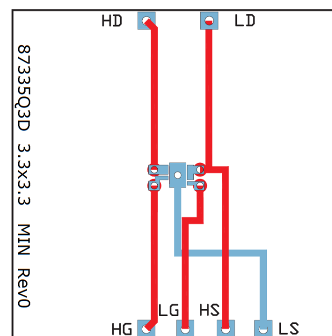
5.5 Electrical Characteristics

T_A = 25°C (unless otherwise stated)

PARAMETER		TEST CONDITIONS	Q1 Control FET			Q2 Sync FET			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
STATIC CHARACTERISTICS									
BV_{DSS}	Drain-to-source voltage	V_{GS} = 0 V, I_{DS} = 250 μA	30			30			V
I_{DSS}	Drain-to-source leakage current	V_{GS} = 0 V, V_{DS} = 24 V			1			1	μA
I_{GSS}	Gate-to-source leakage current	V_{DS} = 0 V, V_{GS} = +10 / –8 V			100			100	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	V_{DS} = V_{GS}, I_{DS} = 250 μA	1.0		1.9	0.75		1.20	V
$Z_{DS(on)}$	Effective AC on-impedance	V_{IN} = 12 V, V_{GS} = 5 V, V_{OUT} = 1.3 V, I_{OUT} = 15 A, f_{SW} = 500 kHz, L_{OUT} = 950 nH		6.7			1.9		mΩ
g_{fs}	Transconductance	V_{DS} = 3 V, I_{DS} = 15 A		59			107		S
DYNAMIC CHARACTERISTICS									
C_{ISS}	Input capacitance	V_{GS} = 0 V, V_{DS} = 15 V, f = 1 MHz		805	1050		1620	2100	pF
C_{OSS}	Output capacitance			412	536		783	1020	pF
C_{RSS}	Reverse transfer capacitance			15	20		28	36	pF
R_G	Series gate resistance			1.2	2.4		0.6	1.2	Ω
Q_g	Gate charge total (4.5 V)	V_{DS} = 15 V, I_{DS} = 15 A		5.7	7.4		10.7	14.0	nC
Q_{gd}	Gate charge – gate-to-drain			1.1			1.7		nC
Q_{gs}	Gate charge – gate-to-source			2.1			2.8		nC
$Q_{g(th)}$	Gate charge at Vth			1.1			1.4		nC
Q_{OSS}	Output charge	V_{DS} = 15 V, V_{GS} = 0 V		11			19		nC
$t_{d(on)}$	Turn on delay time	V_{DS} = 15 V, V_{GS} = 4.5 V, I_{DS} = 15 A, R_G = 2 Ω		8			8		ns
t_r	Rise time			29			27		ns
$t_{d(off)}$	Turn off delay time			13			17		ns
t_f	Fall time			4			5		ns
DIODE CHARACTERISTICS									
V_{SD}	Diode forward voltage	I_{DS} = 15 A, V_{GS} = 0 V		0.8	1.0		0.8	1.0	V
Q_{rr}	Reverse recovery charge	V_{DS} = 15 V, I_F = 15 A, di/dt = 300 A/μs		24			40		nC
t_{rr}	Reverse recovery time			17			22		ns



Max $R_{\theta JA}$ = 73°C/W when mounted on 1 inch^2 (6.45 cm^2) of 2 oz. (0.071 mm thick) Cu.



Max $R_{\theta JA}$ = 135°C/W when mounted on minimum pad area of 2 oz. (0.071 mm thick) Cu.

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5.6 Typical Power Block Device Characteristics

Test Conditions: V_{IN} = 12 V, V_{DD} = 5 V, f_{SW} = 500 kHz, V_{OUT} = 1.3 V, L_{OUT} = 950 nH, I_{OUT} = 25 A, T_J = 125°C, unless stated otherwise.

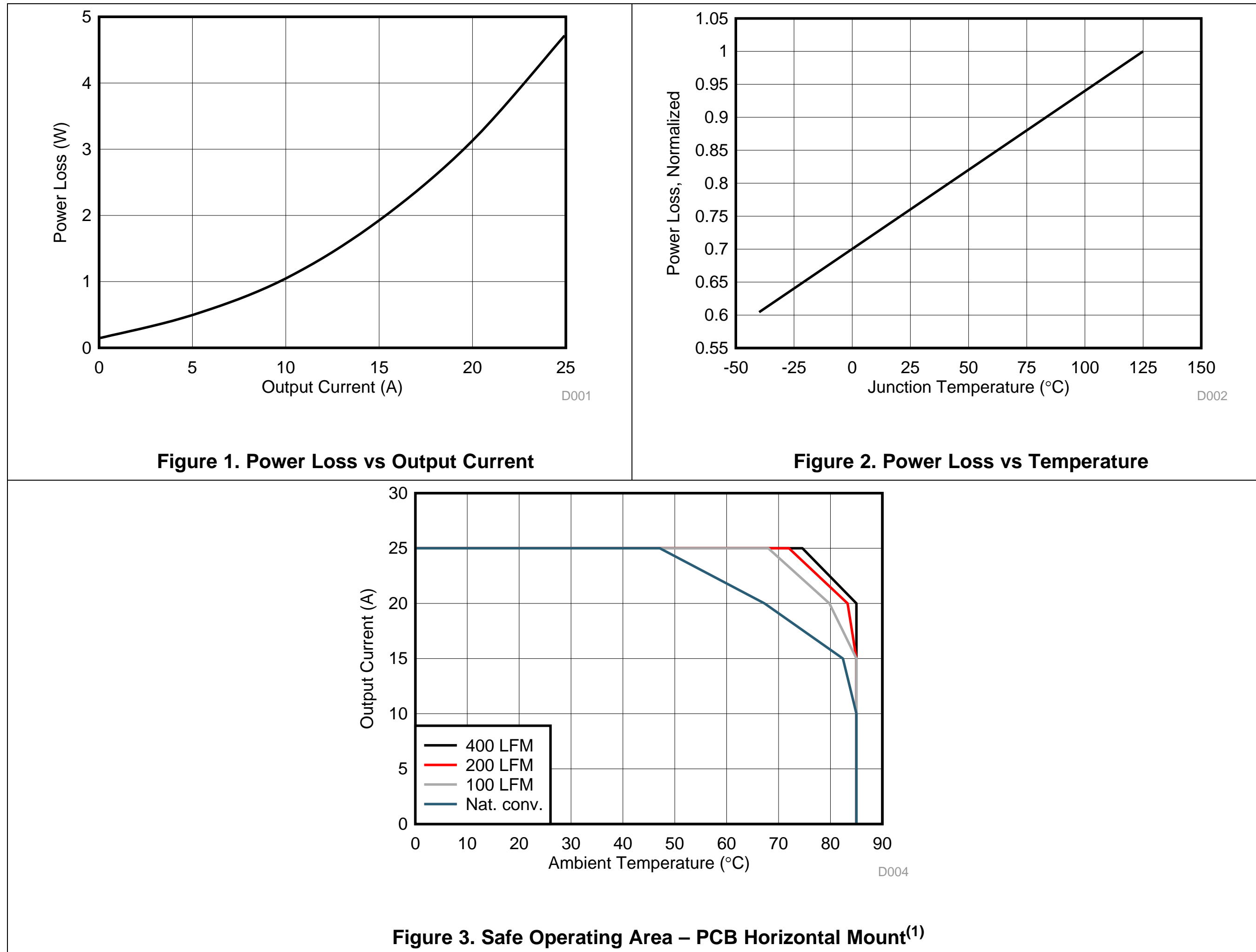

Figure 1. Power Loss vs Output Current

Figure 2. Power Loss vs Temperature

Figure 3. Safe Operating Area – PCB Horizontal Mount(1)

(1) The Typical Power Block System Characteristic curves are based on measurements made on a PCB design with dimensions of 4.0” (W) × 3.5” (L) × 0.062” (H) and 6 copper layers of 1 oz. copper thickness. See Application Section for detailed explanation.

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Typical Power Block Device Characteristics (continued)

Test Conditions: V_{IN} = 12 V, V_{DD} = 5 V, f_{SW} = 500 kHz, V_{OUT} = 1.3 V, L_{OUT} = 950 nH, I_{OUT} = 25 A, T_J = 125°C, unless stated otherwise.

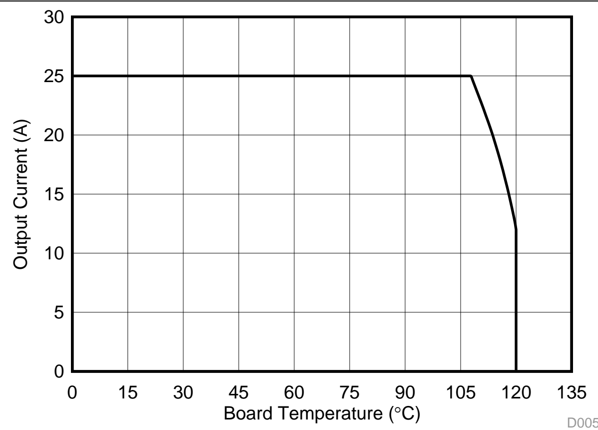

Figure 4. Typical Safe Operating Area(1)

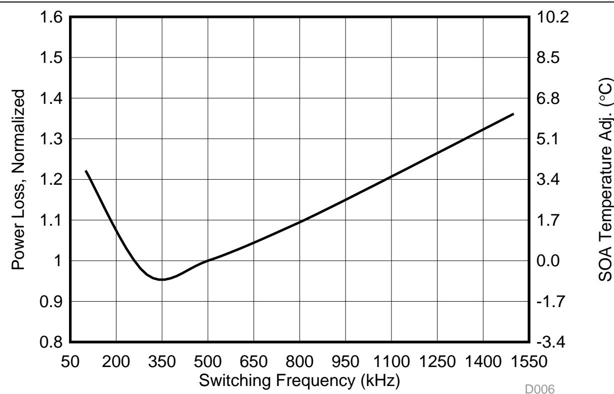

Figure 5. Normalized Power Loss vs Switching Frequency

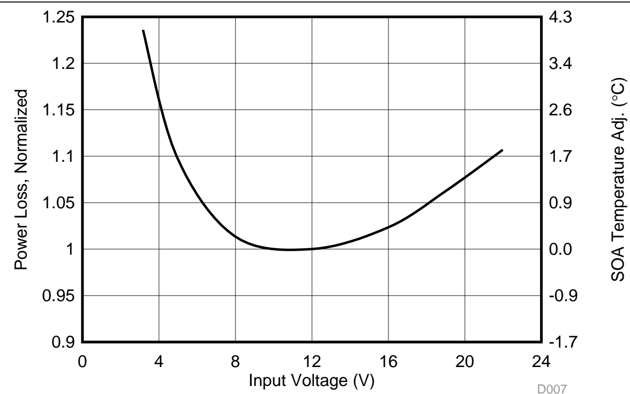

Figure 6. Normalized Power Loss vs Input Voltage

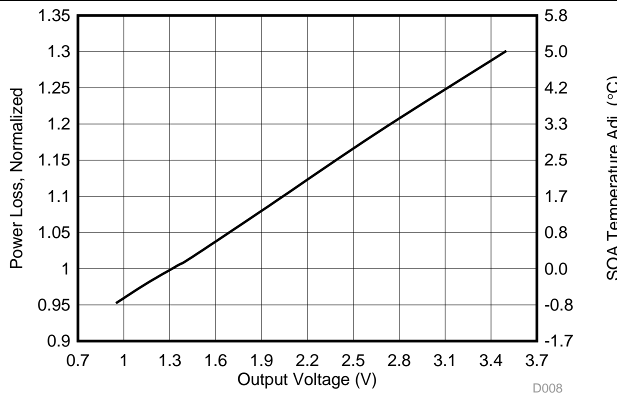

Figure 7. Normalized Power Loss vs. Output Voltage

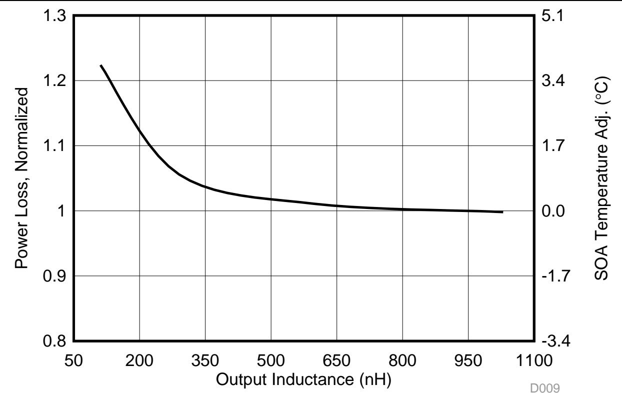

Figure 8. Normalized Power Loss vs. Output Inductance

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5.7 Typical Power Block MOSFET Characteristics

T_A = 25°C, unless stated otherwise.

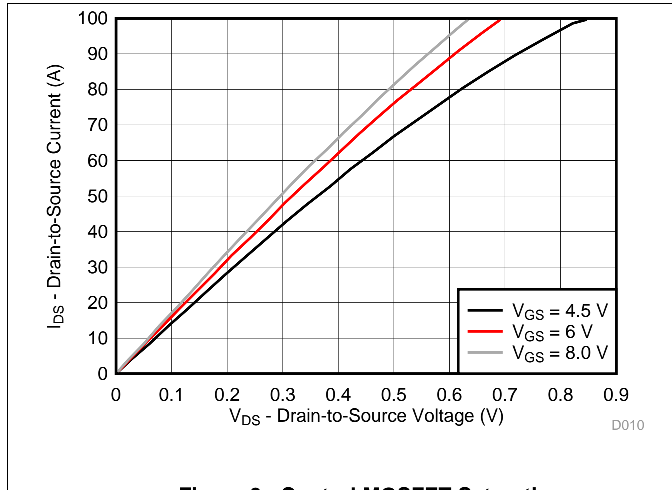


Figure 9. Control MOSFET Saturation

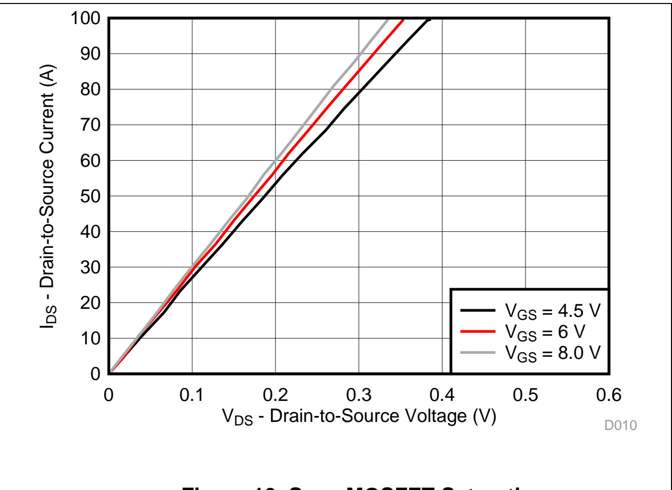
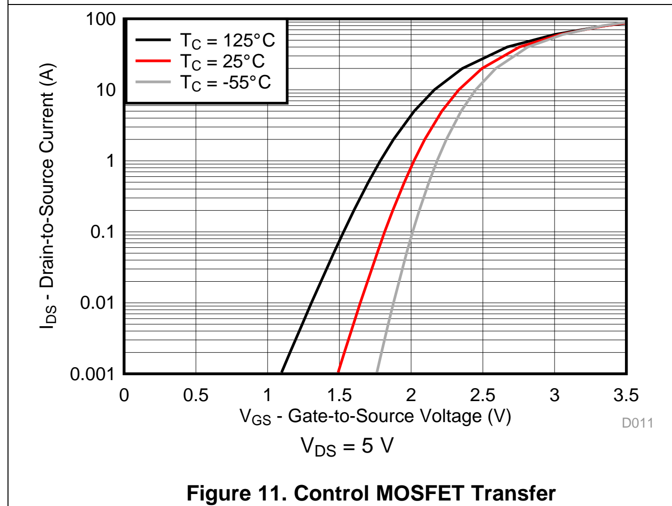
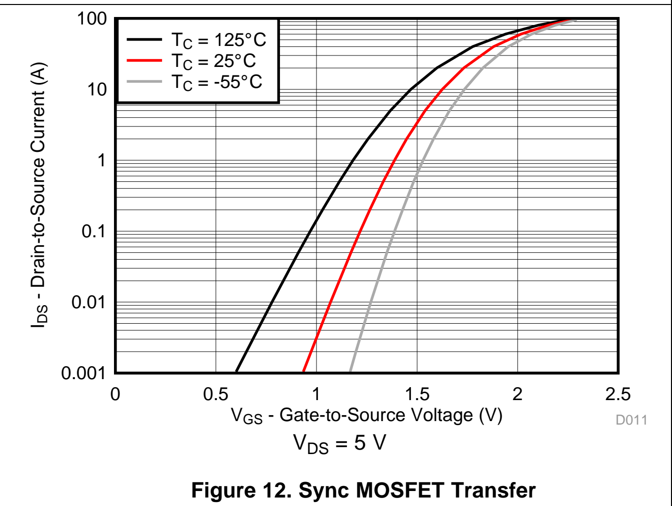


Figure 10. Sync MOSFET Saturation



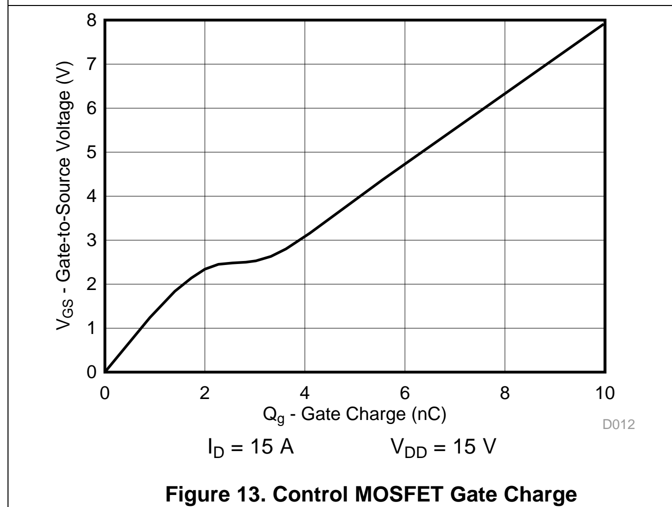
V_{DS} = 5 V

Figure 11. Control MOSFET Transfer



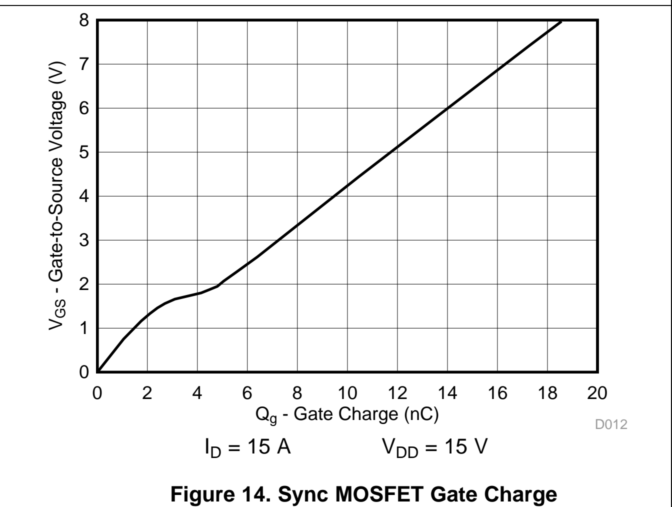
V_{DS} = 5 V

Figure 12. Sync MOSFET Transfer



I_D = 15 A V_{DD} = 15 V

Figure 13. Control MOSFET Gate Charge



I_D = 15 A V_{DD} = 15 V

Figure 14. Sync MOSFET Gate Charge

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Typical Power Block MOSFET Characteristics (continued)

T_A = 25°C, unless stated otherwise.

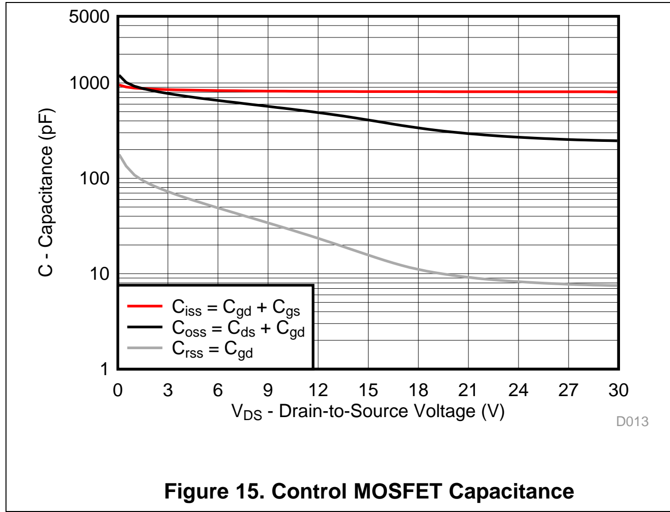


Figure 15. Control MOSFET Capacitance

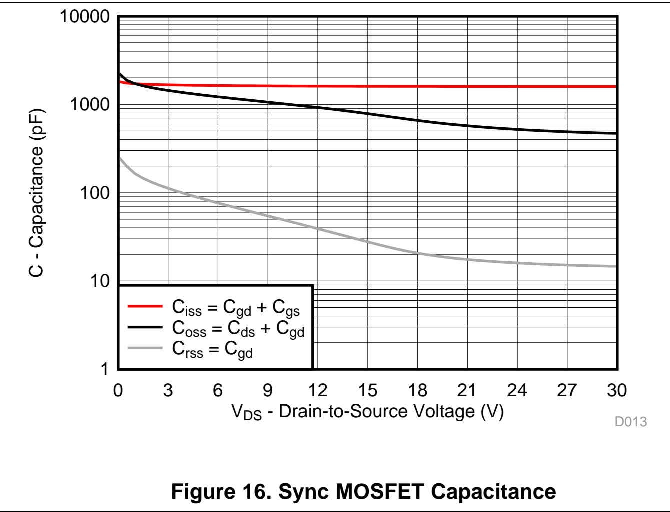
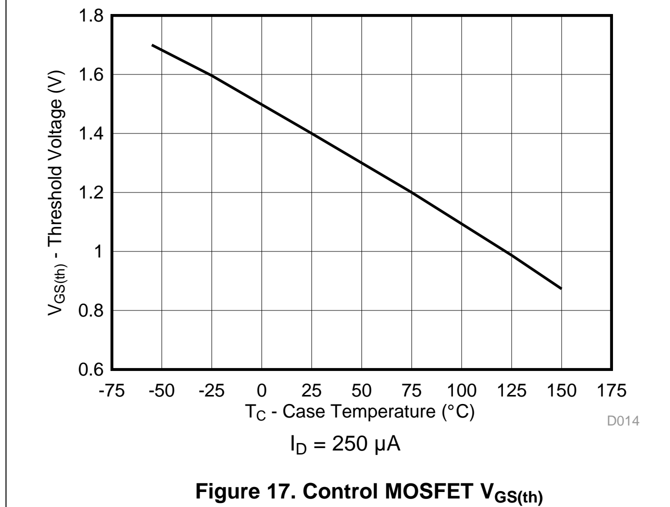
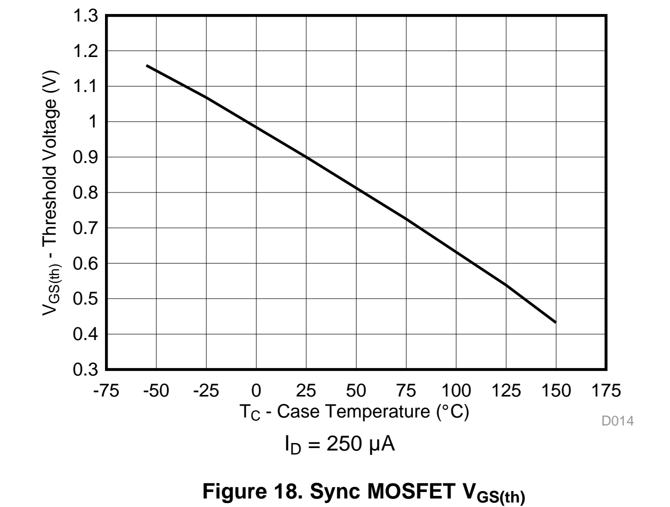


Figure 16. Sync MOSFET Capacitance



I_D = 250 µA

Figure 17. Control MOSFET $V_{GS(th)}$



I_D = 250 µA

Figure 18. Sync MOSFET $V_{GS(th)}$

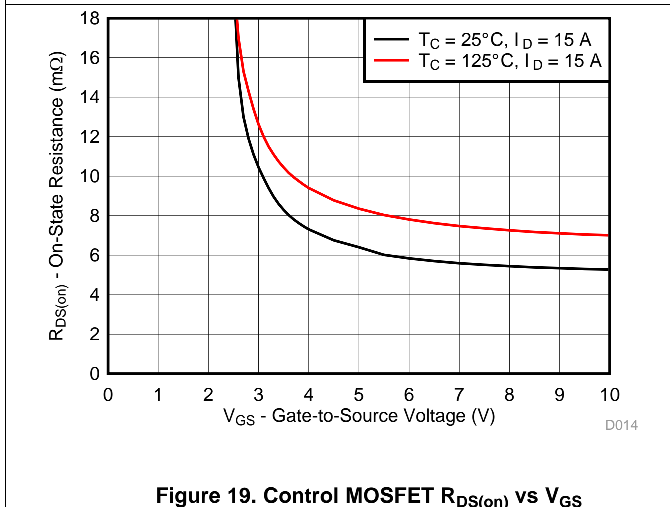


Figure 19. Control MOSFET $R_{DS(on)}$ vs V_{GS}

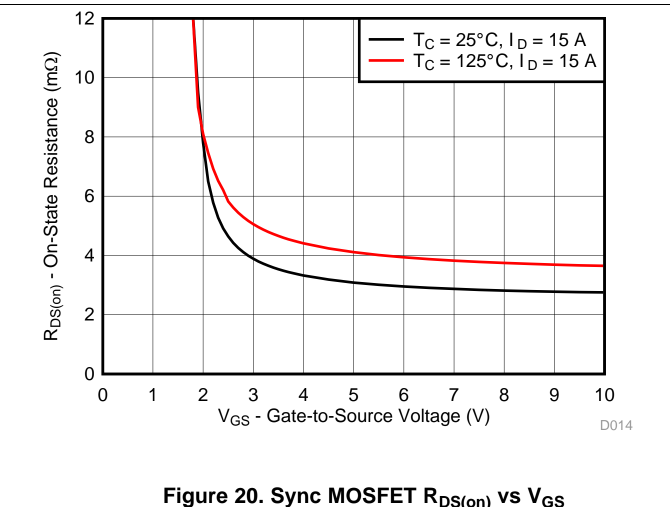


Figure 20. Sync MOSFET $R_{DS(on)}$ vs V_{GS}

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Typical Power Block MOSFET Characteristics (continued)

T_A = 25°C, unless stated otherwise.

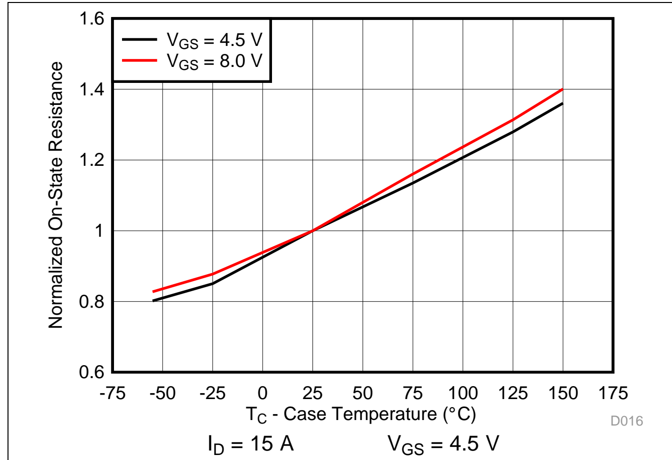

Figure 21. Control MOSFET Normalized $R_{DS(on)}$

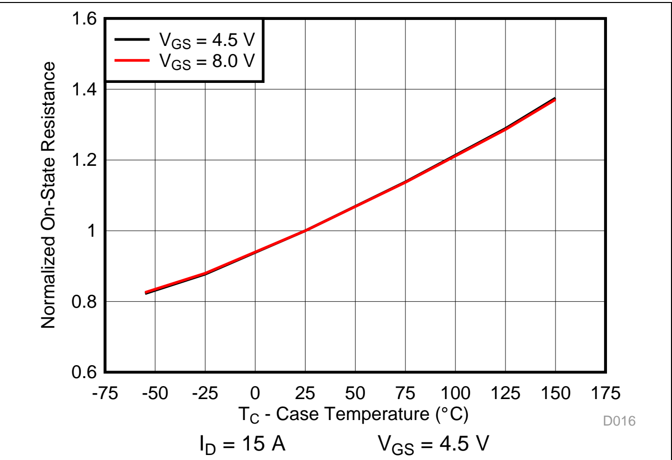

Figure 22. Sync MOSFET Normalized $R_{DS(on)}$

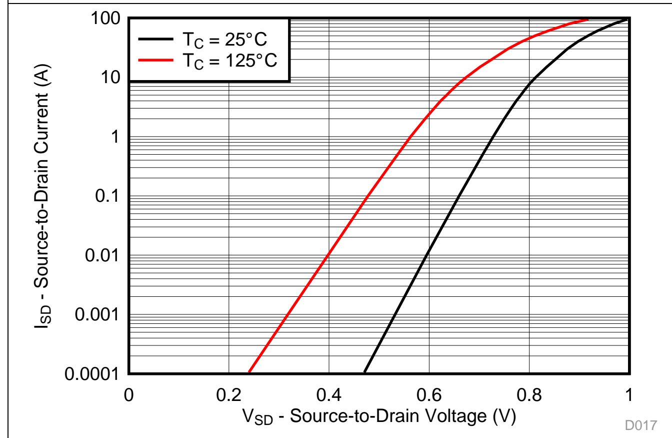

Figure 23. Control MOSFET Body Diode

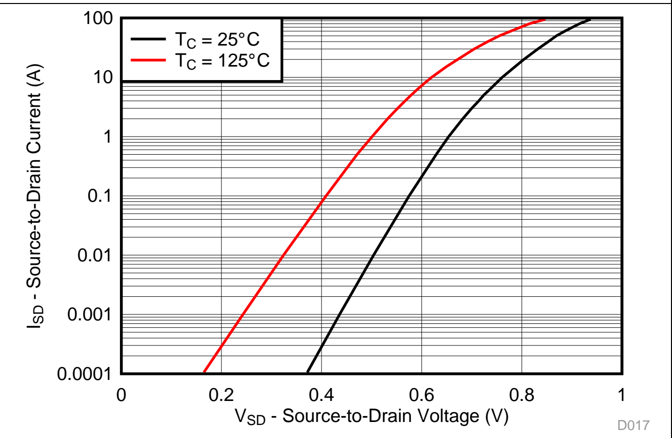

Figure 24. Sync MOSFET Body Diode

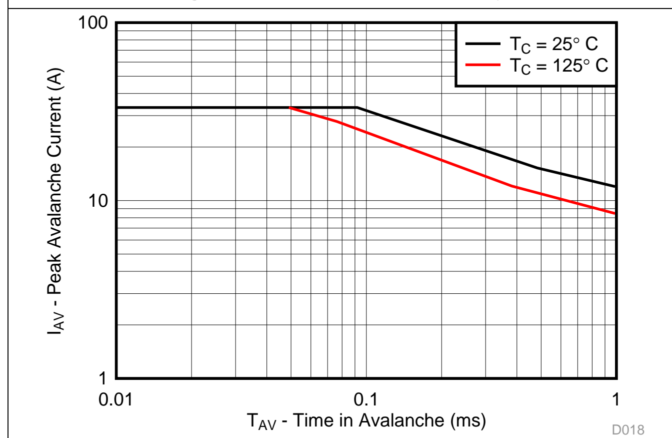

Figure 25. Control MOSFET Unclamped Inductive Switching

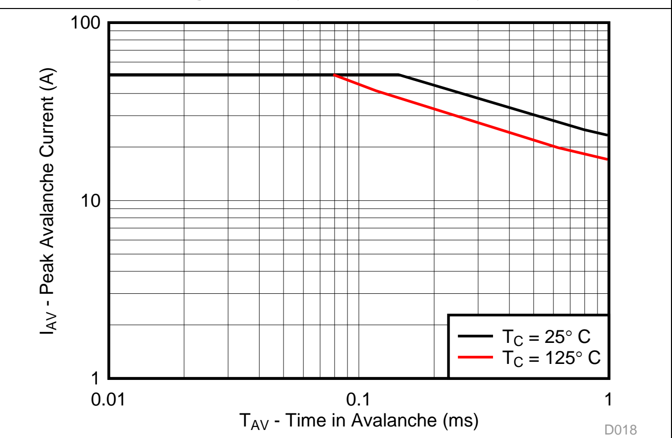

Figure 26. Sync MOSFET Unclamped Inductive Switching

6 Applications and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

6.1 Application Information

6.1.1 Equivalent System Performance

Many of today's high performance computing systems require low power consumption in an effort to reduce system operating temperatures and improve overall system efficiency. This has created a major emphasis on improving the conversion efficiency of today's Synchronous Buck Topology. In particular, there has been an emphasis in improving the performance of the critical Power Semiconductor in the Power Stage of this Application (see Figure 27). As such, optimization of the power semiconductors in these applications, needs to go beyond simply reducing $R_{DS(ON)}$.

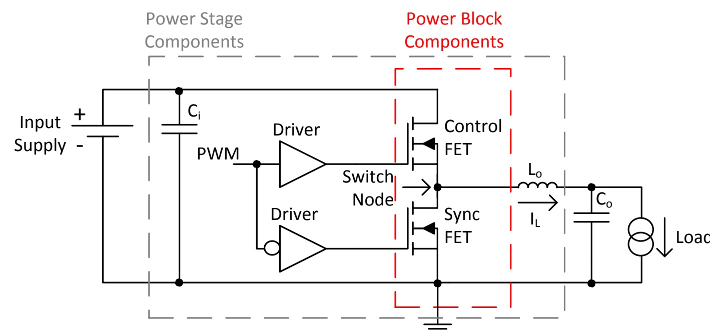

Figure 27.

The CSD87335Q3D is part of TI's Power Block product family which is a highly optimized product for use in a synchronous buck topology requiring high current, high efficiency, and high frequency. It incorporates TI's latest generation silicon which has been optimized for switching performance, as well as minimizing losses associated with Q_{GD}, Q_{GS}, and Q_{RR}. Furthermore, TI's patented packaging technology has minimized losses by nearly eliminating parasitic elements between the Control FET and Sync FET connections (see Figure 28). A key challenge solved by TI's patented packaging technology is the system level impact of Common Source Inductance (CSI). CSI greatly impedes the switching characteristics of any MOSFET which in turn increases switching losses and reduces system efficiency. As a result, the effects of CSI need to be considered during the MOSFET selection process. In addition, standard MOSFET switching loss equations used to predict system efficiency need to be modified in order to account for the effects of CSI. Further details behind the effects of CSI and modification of switching loss equations are outlined in TI's Application Note SLPA009.

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Application Information (continued)

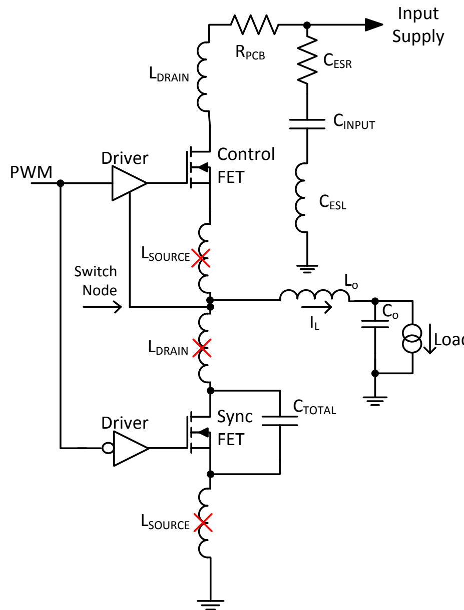

Figure 28.

The combination of TI's latest generation silicon and optimized packaging technology has created a benchmarking solution that outperforms industry standard MOSFET chipsets of similar $R_{DS(ON)}$ and MOSFET chipsets with lower $R_{DS(ON)}$. Figure 29 and Figure 30 compare the efficiency and power loss performance of the CSD87335Q3D versus industry standard MOSFET chipsets commonly used in this type of application. This comparison purely focuses on the efficiency and generated loss of the power semiconductors only. The performance of CSD87335Q3D clearly highlights the importance of considering the Effective AC On-Impedance ($Z_{DS(ON)}$) during the MOSFET selection process of any new design. Simply normalizing to traditional MOSFET $R_{DS(ON)}$ specifications is not an indicator of the actual in-circuit performance when using TI's Power Block technology.

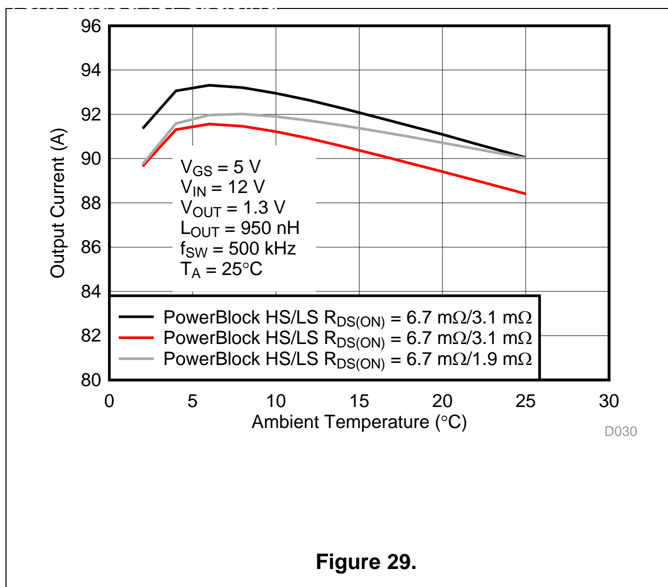

Figure 29.

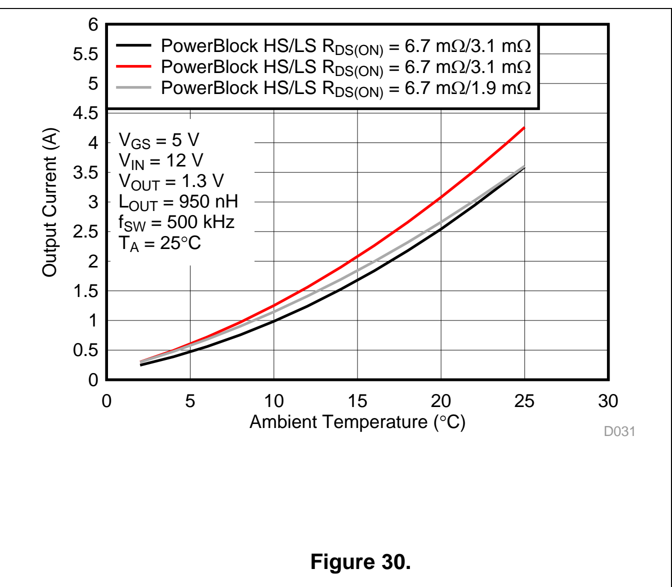

Figure 30.

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Table 1 compares the traditional DC measured $R_{DS(ON)}$ of CSD87335Q3D versus its $Z_{DS(ON)}$. This comparison takes into account the improved efficiency associated with TI's patented packaging technology. As such, when comparing TI's Power Block products to individually packaged discrete MOSFETs or dual MOSFETs in a standard package, the in-circuit switching performance of the solution must be considered. In this example, individually packaged discrete MOSFETs or dual MOSFETs in a standard package would need to have DC measured $R_{DS(ON)}$ values that are equivalent to CSD87335Q3D's $Z_{DS(ON)}$ value in order to have the same efficiency performance at full load. Mid to light-load efficiency will still be lower with individually packaged discrete MOSFETs or dual MOSFETs in a standard package.

Table 1. Comparison of $R_{DS(ON)}$ vs. $Z_{DS(ON)}$

Parameter	HS		LS	
	Typ	Max	Typ	Max
Effective AC On-Impedance $Z_{DS(ON)}$ (V_{GS} = 5 V)	6.7	-	1.9	-
DC Measured $R_{DS(ON)}$ (V_{GS} = 4.5 V)	6.7	8.1	3.1	3.9

The CSD87335Q3D NexFET™ power block is an optimized design for synchronous buck applications using 5 V gate drive. The Control FET and Sync FET silicon are parametrically tuned to yield the lowest power loss and highest system efficiency. As a result, a new rating method is needed which is tailored towards a more systems centric environment. System level performance curves such as Power Loss, Safe Operating Area, and normalized graphs allow engineers to predict the product performance in the actual application.

6.2 Power Loss Curves

MOSFET centric parameters such as $R_{DS(ON)}$ and Q_{gd} are needed to estimate the loss generated by the devices. In an effort to simplify the design process for engineers, Texas Instruments has provided measured power loss performance curves. Figure 1 plots the power loss of the CSD87335Q3D as a function of load current. This curve is measured by configuring and running the CSD87335Q3D as it would be in the final application (see Figure 31).The measured power loss is the CSD87335Q3D loss and consists of both input conversion loss and gate drive loss. Equation 1 is used to generate the power loss curve.

$$(V_{IN} \times I_{IN}) + (V_{DD} \times I_{DD}) - (V_{SW_AVG} \times I_{OUT}) = \text{Power Loss} \quad (1)$$

The power loss curve in Figure 1 is measured at the maximum recommended junction temperatures of 125°C under isothermal test conditions.

6.3 Safe Operating Curves (SOA)

The SOA curves in the CSD87335Q3D data sheet provides guidance on the temperature boundaries within an operating system by incorporating the thermal resistance and system power loss. to Figure 4 outline the temperature and airflow conditions required for a given load current. The area under the curve dictates the safe operating area. All the curves are based on measurements made on a PCB design with dimensions of 4" (W) × 3.5" (L) × 0.062" (T) and 6 copper layers of 1 oz. copper thickness.

6.4 Normalized Curves

The normalized curves in the CSD87335Q3D data sheet provides guidance on the Power Loss and SOA adjustments based on their application specific needs. These curves show how the power loss and SOA boundaries will adjust for a given set of systems conditions. The primary Y-axis is the normalized change in power loss and the secondary Y-axis is the change is system temperature required in order to comply with the SOA curve. The change in power loss is a multiplier for the Power Loss curve and the change in temperature is subtracted from the SOA curve.

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Normalized Curves (continued)

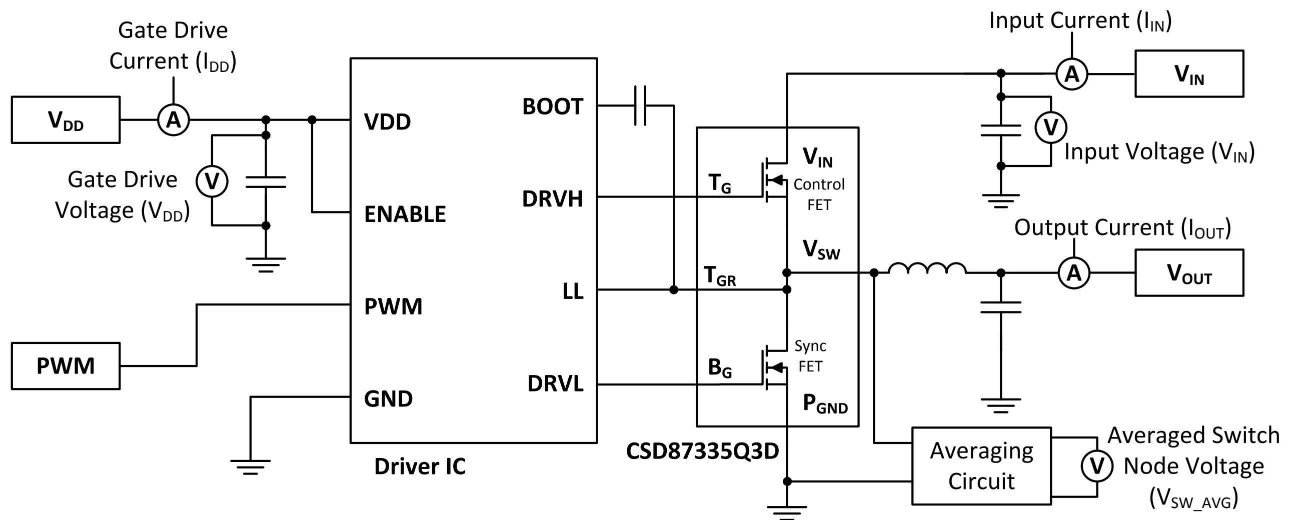

Figure 31. Typical Application

6.5 Calculating Power Loss and SOA

The user can estimate product loss and SOA boundaries by arithmetic means (see *Design Example*). Though the Power Loss and SOA curves in this data sheet are taken for a specific set of test conditions, the following procedure will outline the steps the user should take to predict product performance for any set of system conditions.

6.5.1 Design Example

Operating Conditions:

- Output Current = 15 A
- Input Voltage = 14 V
- Output Voltage = 1.4 V
- Switching Frequency = 750 kHz
- Inductor = 600 nH

6.5.2 Calculating Power Loss

- Power Loss at 15 A = 1.92 W (Figure 1)
- Normalized Power Loss for input voltage ≈ 1.01 (Figure 6)
- Normalized Power Loss for output voltage ≈ 1.01 (Figure 7)
- Normalized Power Loss for switching frequency ≈ 1.08 (Figure 5)
- Normalized Power Loss for output inductor ≈ 1.01 (Figure 8)
- **Final calculated Power Loss = 1.92 W × 1.01 × 1.01 × 1.08 × 1.01 ≈ 2.14 W**

6.5.3 Calculating SOA Adjustments

- SOA adjustment for input voltage ≈ 0.14ºC (Figure 6)
- SOA adjustment for output voltage ≈ 0.17ºC (Figure 7)
- SOA adjustment for switching frequency ≈ 1.32ºC (Figure 5)
- SOA adjustment for output inductor ≈ 0.18ºC (Figure 8)
- **Final calculated SOA adjustment = 0.14 + 0.17 + 1.32 + 0.18 ≈ 1.81ºC**

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Calculating Power Loss and SOA (continued)

In the design example above, the estimated power loss of the CSD87335Q3D would increase to 2.14 W. In addition, the maximum allowable board and/or ambient temperature would have to decrease by 1.81ºC. Figure 32 graphically shows how the SOA curve would be adjusted accordingly.

1. Start by drawing a horizontal line from the application current to the SOA curve.
2. Draw a vertical line from the SOA curve intercept down to the board/ambient temperature.
3. Adjust the SOA board/ambient temperature by subtracting the temperature adjustment value.

In the design example, the SOA temperature adjustment yields a reduction in allowable board/ambient temperature of 1.81ºC. In the event the adjustment value is a negative number, subtracting the negative number would yield an increase in allowable board/ambient temperature.

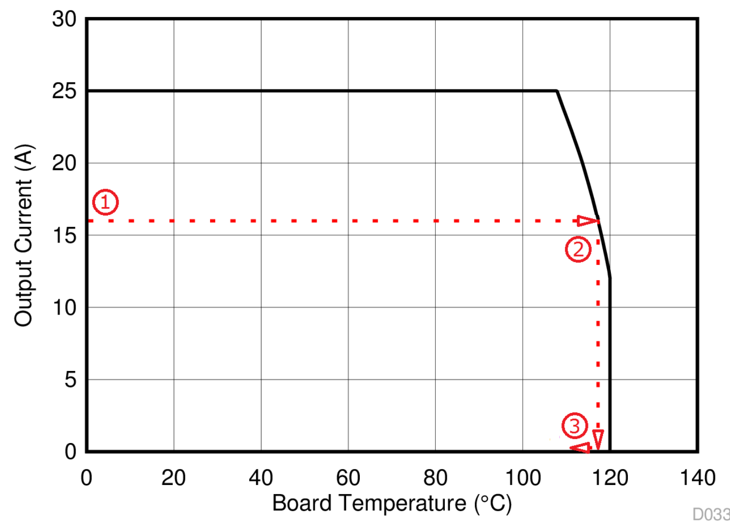

Figure 32. Power Block SOA

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7 Recommended PCB Design Overview

There are two key system-level parameters that can be addressed with a proper PCB design: Electrical and Thermal performance. Properly optimizing the PCB layout will yield maximum performance in both areas. A brief description on how to address each parameter is provided.

7.1 Electrical Performance

The Power Block has the ability to switch voltages at rates greater than 10 kV/µs. Special care must be then taken with the PCB layout design and placement of the input capacitors, Driver IC, and output inductor.

- The placement of the input capacitors relative to the Power Block's VIN and PGND pins should have the highest priority during the component placement routine. It is critical to minimize these node lengths. As such, ceramic input capacitors need to be placed as close as possible to the VIN and PGND pins (see Figure 33). The example in Figure 33 uses 6 × 10 µF ceramic capacitors (TDK Part # C3216X5R1C106KT or equivalent). Notice there are ceramic capacitors on both sides of the board with an appropriate amount of vias interconnecting both layers. In terms of priority of placement next to the Power Block, C5, C7, C19, and C8 should follow in order.
- The Driver IC should be placed relatively close to the Power Block Gate pins. T_G and B_G should connect to the outputs of the Driver IC. The T_{GR} pin serves as the return path of the high-side gate drive circuitry and should be connected to the Phase pin of the IC (sometimes called LX, LL, SW, PH, etc.). The bootstrap capacitor for the Driver IC will also connect to this pin.
- The switching node of the output inductor should be placed relatively close to the Power Block VSW pins. Minimizing the node length between these two components will reduce the PCB conduction losses and actually reduce the switching noise level. In the event the switch node waveform exhibits ringing that reaches undesirable levels, the use of a Boost Resistor or RC snubber can be an effective way to easily reduce the peak ring level. The recommended Boost Resistor value will range between 1.0 Ohms to 4.7 Ohms depending on the output characteristics of Driver IC used in conjunction with the Power Block. The RC snubber values can range from 0.5 Ohms to 2.2 Ohms for the R and 330 pF to 2200 pF for the C. Please refer to TI App Note SLUP100 for more details on how to properly tune the RC snubber values. The RC snubber should be placed as close as possible to the Vsw node and PGND (see Figure 33). [(1)]

(1) Keong W. Kam, David Pommerenke, "EMI Analysis Methods for Synchronous Buck Converter EMI Root Cause Analysis", University of Missouri – Rolla

7.2 Thermal Performance

The Power Block has the ability to utilize the GND planes as the primary thermal path. As such, the use of thermal vias is an effective way to pull away heat from the device and into the system board. Concerns of solder voids and manufacturability problems can be addressed by the use of three basic tactics to minimize the amount of solder attach that will wick down the via barrel:

- Intentionally space out the vias from each other to avoid a cluster of holes in a given area.
- Use the smallest drill size allowed in your design. The example in Figure 33 uses vias with a 10 mil drill hole and a 16 mil capture pad.
- Tent the opposite side of the via with solder-mask.

In the end, the number and drill size of the thermal vias should align with the end user's PCB design rules and manufacturing capabilities.

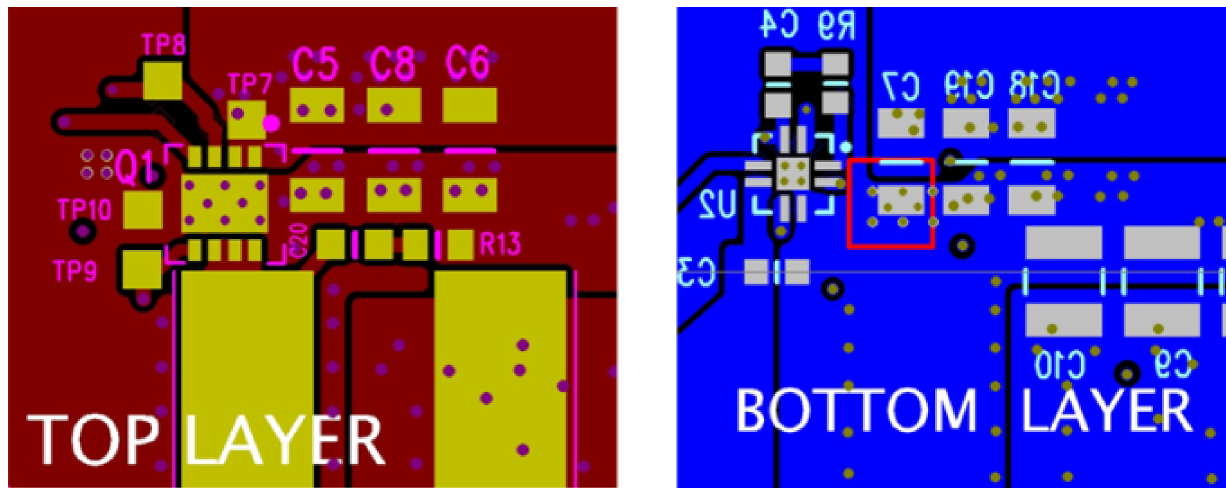

Figure 33. Recommended PCB Layout (Top Down)

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8 器件和文档支持

8.1 社区资源

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Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

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8.3 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

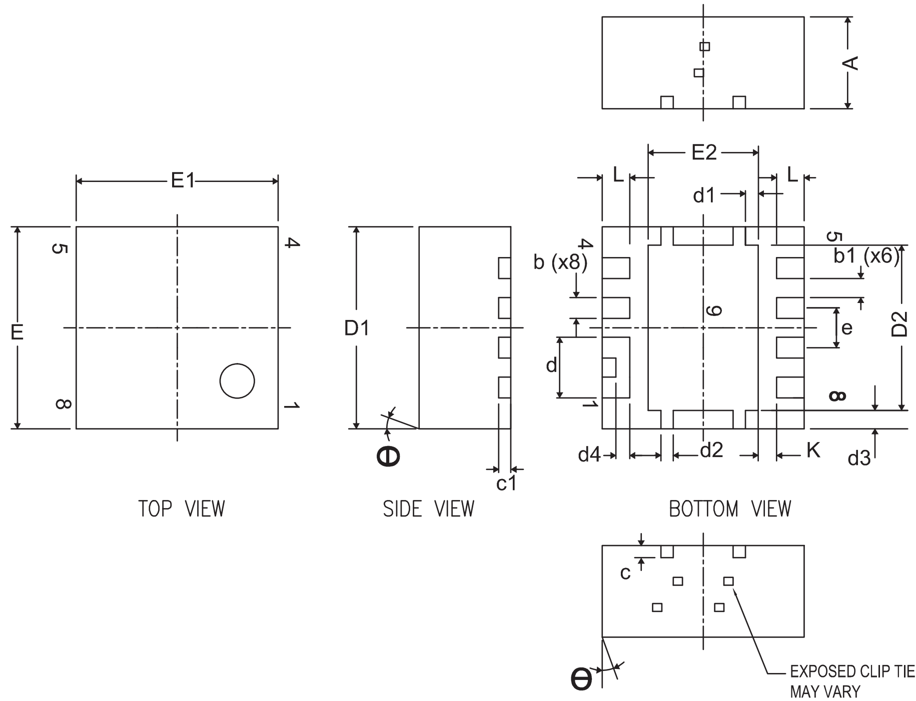
8.4 Glossary

SLYZ022 — *TI Glossary*.
This glossary lists and explains terms, acronyms, and definitions.

9 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。要获得这份数据表的浏览器版本，请查阅左侧的导航栏。

9.1 Q3D 封装尺寸



DIM	毫米		英寸	
	最小值	最大值	最小值	最大值
A	1.400	1.500	0.055	0.059
b	0.280	0.400	0.011	0.016
b1	0.310（标称值）		0.012（标称值）	
c	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
d	0.940	1.040	0.037	0.041
d1	0.160	0.260	0.006	0.010
d2	0.150	0.250	0.006	0.010
d3	0.250	0.350	0.010	0.014
d4	0.175	0.275	0.007	0.011
D1	3.200	3.400	0.126	0.134
D2	2.650	2.750	0.104	0.108
E	3.200	3.400	0.126	0.134
E1	3.200	3.400	0.126	0.134
E2	1.750	1.850	0.069	0.073
e	0.650 典型值		0.026 典型值	
L	0.400	0.500	0.016	0.020
θ	0.00	-	-	-
K	0.300 典型值		0.012 典型值	

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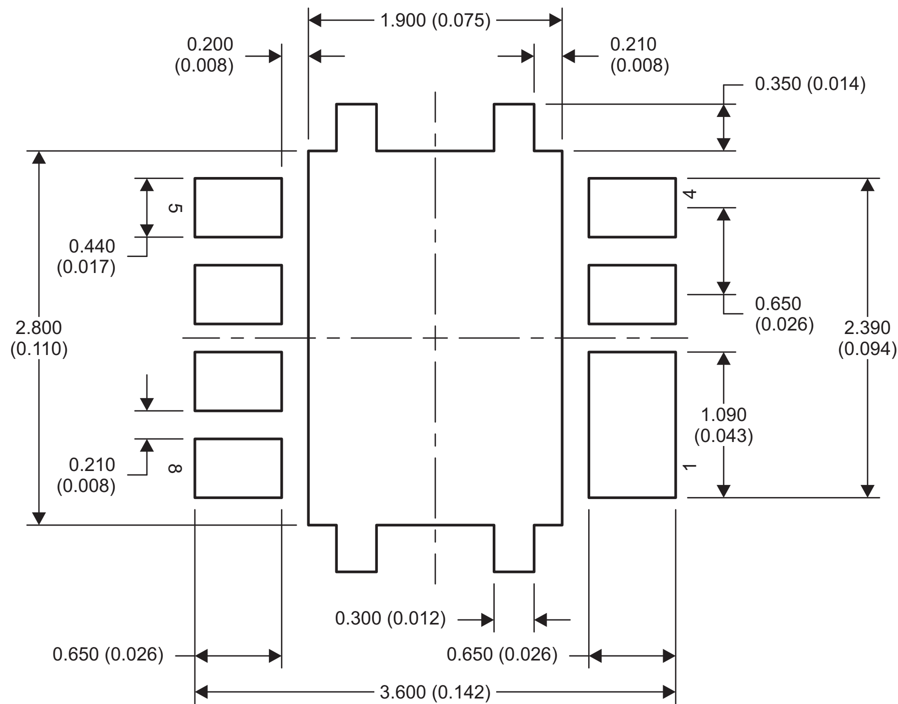
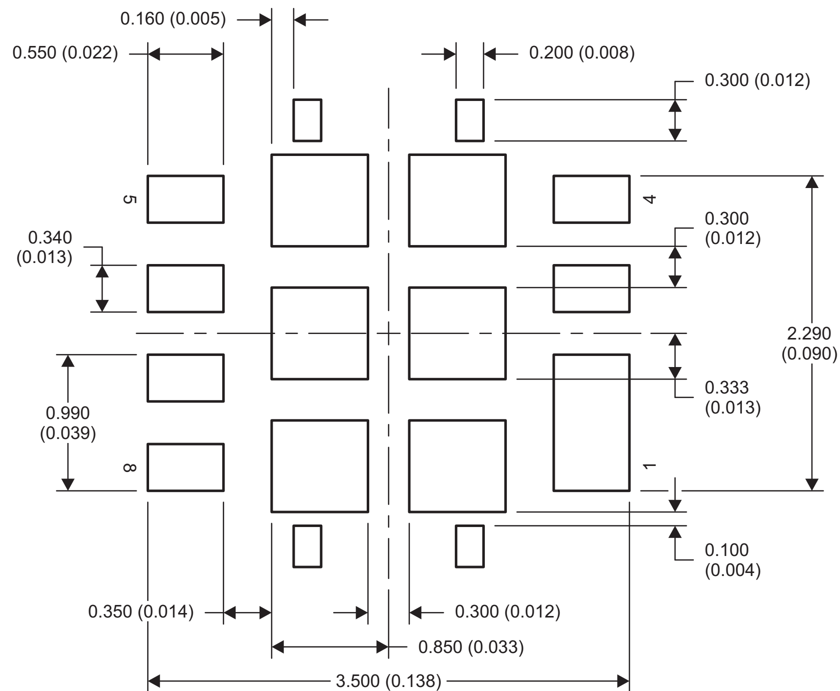
9.2 焊盘布局建议



NOTE：尺寸单位为 mm（英寸）。

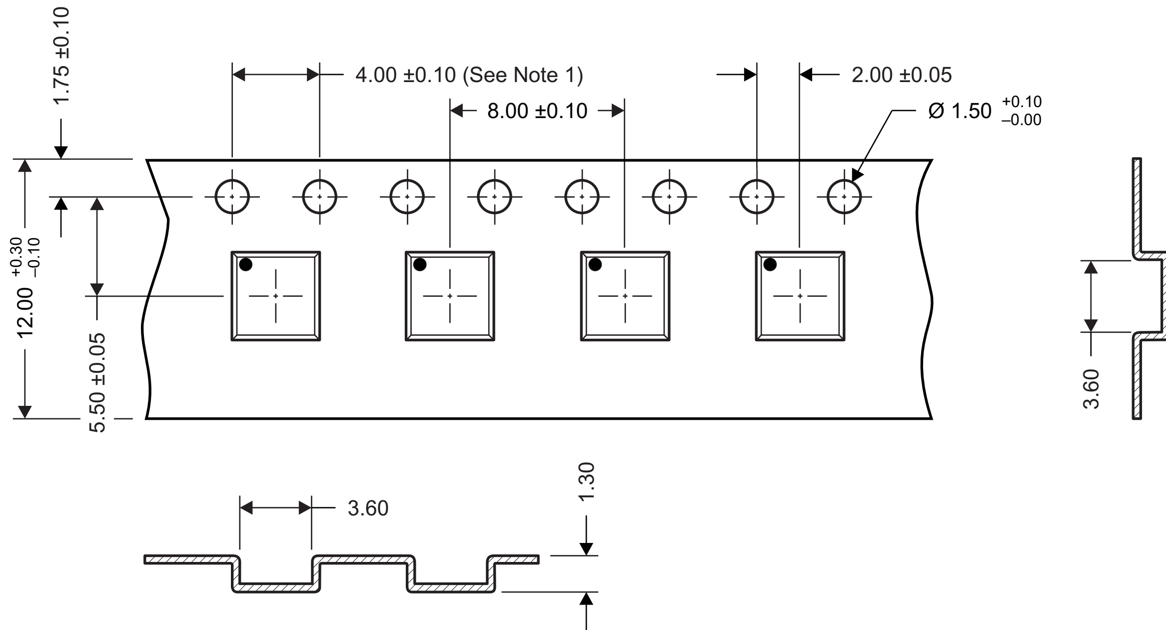
9.3 模板建议



NOTE：尺寸单位为 mm（英寸）。

要获得与印刷电路板 (PCB) 设计相关的电路布局布线建议，请参见《应用说明》文献编号：SLPA005 - *通过 PCB 布局布线技巧来减少振铃*

9.4 Q3D 卷带信息



NOTES: 1. 10 个链齿孔的累积容差为 ±0.2

2. 每 100mm 长度的翘曲不能超过 1mm，250mm 长度的非累积量 (Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm)

3. 材料：黑色抗静电聚苯乙烯

4. 全部尺寸单位为 mm，除非另外注明。

5. 厚度：0.30 ± 0.05mm

6. MSL1 260°C（红外 (IR) 和传导）PbF 回流焊兼容

9.5 引脚配置

位置	名称
引脚 1	V_{IN}
引脚 2	V_{IN}
引脚 3	T_G
引脚 4	T_{GR}
引脚 5	B_G
引脚 6	V_{SW}
引脚 7	V_{SW}
引脚 8	V_{SW}
引脚 9	P_{GND}

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD87335Q3D	ACTIVE	LSON-CLIP	DQZ	8	2500	Pb-Free (RoHS Exempt)	CU NIPDAU | CU SN	Level-1-260C-UNLIM	-55 to 150	87335D	Samples
CSD87335Q3DT	ACTIVE	LSON-CLIP	DQZ	8	250	Pb-Free (RoHS Exempt)	CU NIPDAU | CU SN	Level-1-260C-UNLIM	-55 to 150	87335D	Samples

[1] The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

[2] Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

[3] MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

[4] There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

[5] Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

[6] Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
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